DERWENT-ACC-NO: 1997-130734

DERWENT-WEEK: 199712

TITLE: Light diode matrix manufacture with x-y coordinate addressing - involves formation of address p-rails on base containing gallium alloy by zone melting and recrystallisation

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PRIORITY-DATA: 1986SU-4050883 (February 6, 1986)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
SU 1347831 A1	July 10, 1996	N/A	002	H01L 033/00

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
SU 1347831A1	N/A	1986SU-4050883	February 6, 1986

INT-CL (IPC): H01L033/00

ABSTRACTED-PUB-NO: SU 1347831A

BASIC-ABSTRACT:

Address p-rails in x direction are made by zone melting using a temp gradient perpendicular to the base (1) plane. The working elements (6) on the face side are made by local thermal oxidation across the epitaxial layer thickness at the temp of 1033 - 1073 deg. K in the nitrogen-oxygen mixture

containing 40 -60 %
of oxygen. These elements are subject to conventional switching in the y
direction at the epitaxial layer side. The address p-rails are formed by local
application of the masking layer on the base made of gallium alloy containing
germanium or zinc in the quantity of 2 - 4 %. The temp gradient is 20 - 40 deg.
K / cm and the recrystallisation rate is 5 - 200 microns per hour.

USE/ADVANTAGE - Method is used in manufacture of integrated semiconductor
circuits. Percentage of good products is increased.

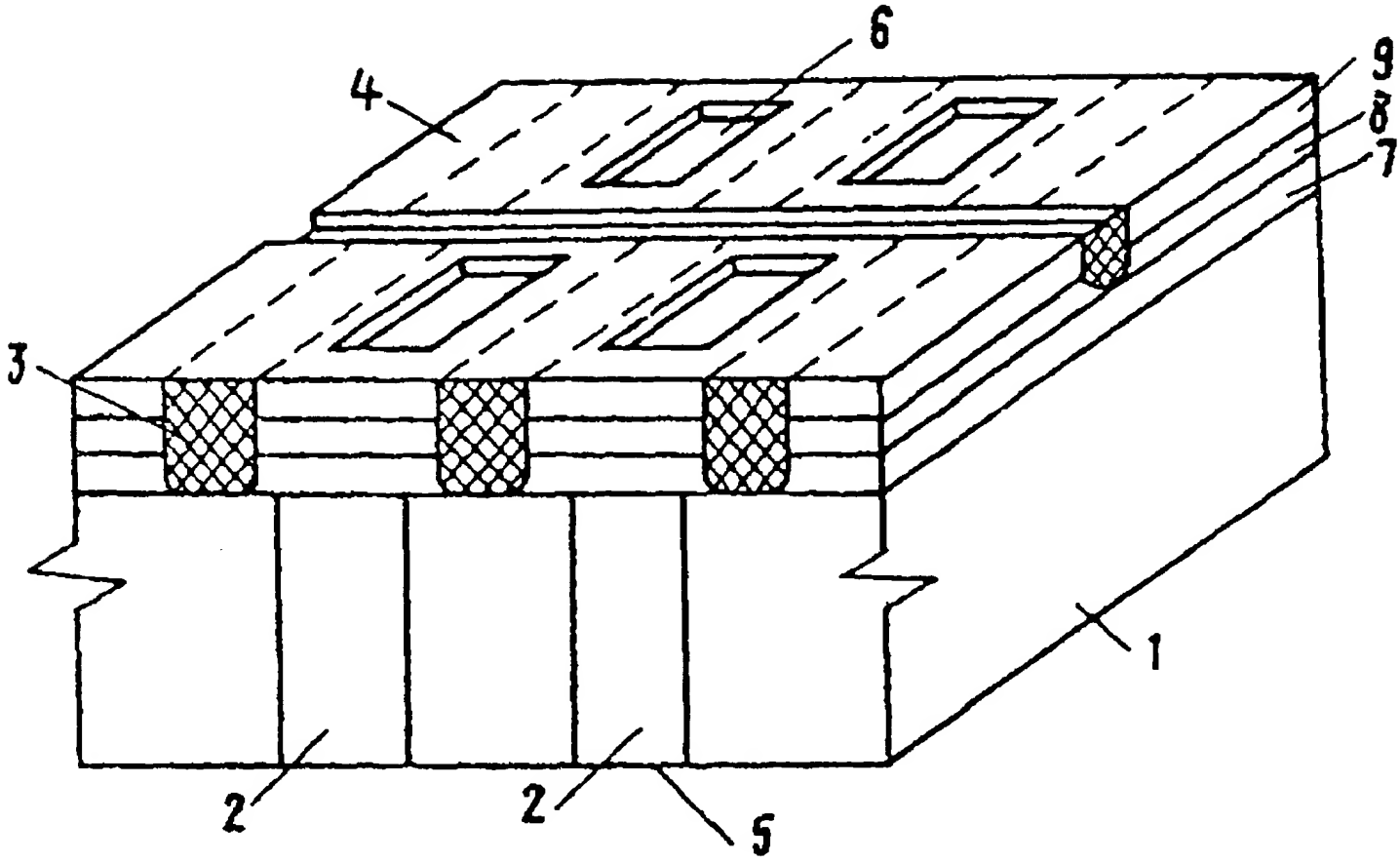
CHOSEN-DRAWING: Dwg.1/1

TITLE-TERMS: LIGHT DIODE MATRIX MANUFACTURE COORDINATE ADDRESS FORMATION
ADDRESS P RAIL BASE CONTAIN GALLIUM ALLOY ZONE MELT
RECRYSTALLISATION

DERWENT-CLASS: U12

EPI-CODES: U12-A01A1A; U12-A01A3;

SECONDARY-ACC-NO:
Non-CPI Secondary Accession Numbers: N1997-108008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